

BCR25RM-12LB

Triac

Medium Power Use

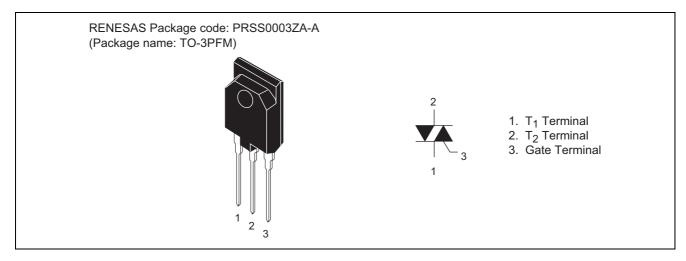
REJ03G1715-0100 Rev.1.00 Jul 10, 2008

Features

- I_{T (RMS)}: 25 A
 V_{DRM}: 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTIII} : 50 mA
- V_{iso}: 2000 V

- The product guaranteed maximum junction temperature of 150°C
- Insulated Type
- Planar Type

Outline



Applications

Contactless AC switch, electric heater control, light dimmer, on/off and speed control of small induction motor, on/off control of copier lamp

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Farameter	Symbol	12	Offic	
Repetitive peak off-state voltage Note1	V_{DRM}	600	V	
Non-repetitive peak off-state voltage Note1	V_{DSM}	720	V	

Notes: 1. Gate open.

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	25	А	Commercial frequency, sine full wave 360° conduction, Tc = 96°C
Surge on-state current	I _{TSM}	250	А	50 Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusion	l ² t	313	A ² s	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	Α	
Junction Temperature	Tj	-40 to +150	°C	
Storage temperature	Tstg	-40 to +150	°C	
Mass	_	5.2	g	Typical value
Isolation voltage	V _{iso}	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Electrical Characteristics

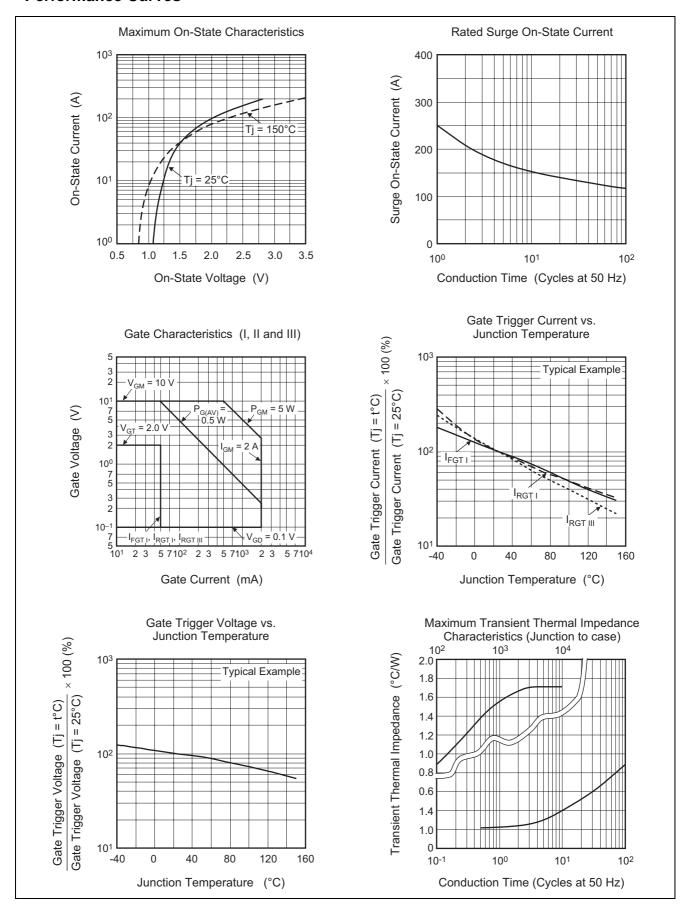
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state of	current	I _{DRM}	_	_	3.0/5.0	mA	Tj = 125°C /150°C, V _{DRM} applied
On-state voltage		V_{TM}	_		1.5	V	Tc = 25°C, I _{TM} = 40 A, instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	_	_	2.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	V_{RGTI}	_		2.0	٧	$R_G = 330 \Omega$
	III	V_{RGTIII}		_	2.0	V	
Gate trigger curent ^{Note2}	I	I_{FGTI}	_	_	50	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	I_{RGTI}	_	_	50	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	50	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	_	_	V	$Tj = 125^{\circ}C / 150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	1.7	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutation voltage ^{Note4}		(dv/dt)c	10/1		_	V/μs	Tj = 125°C /150°C

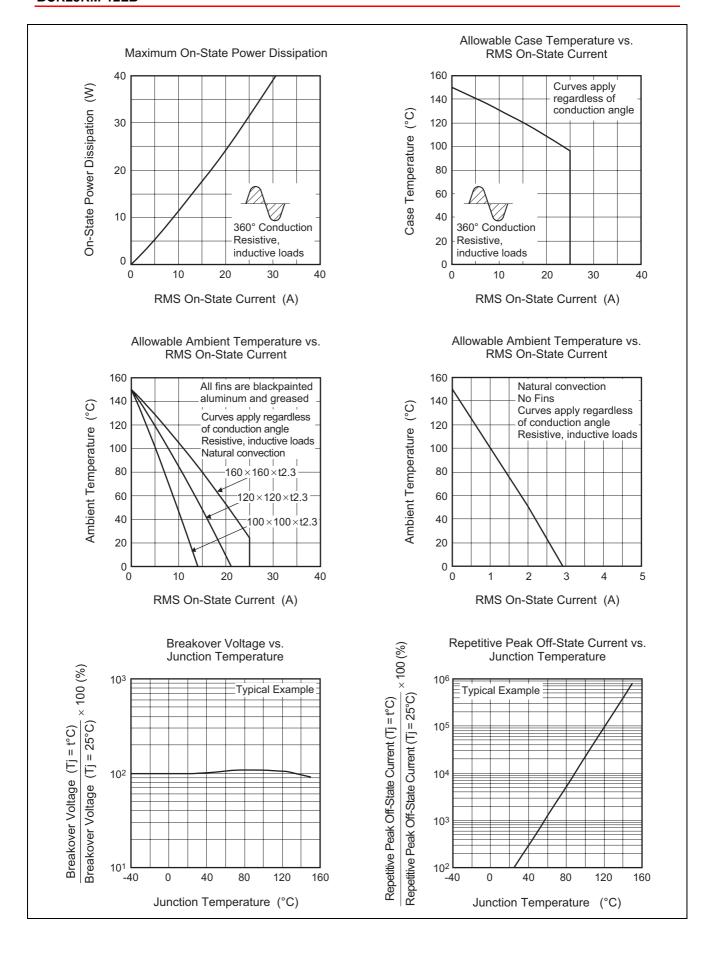
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

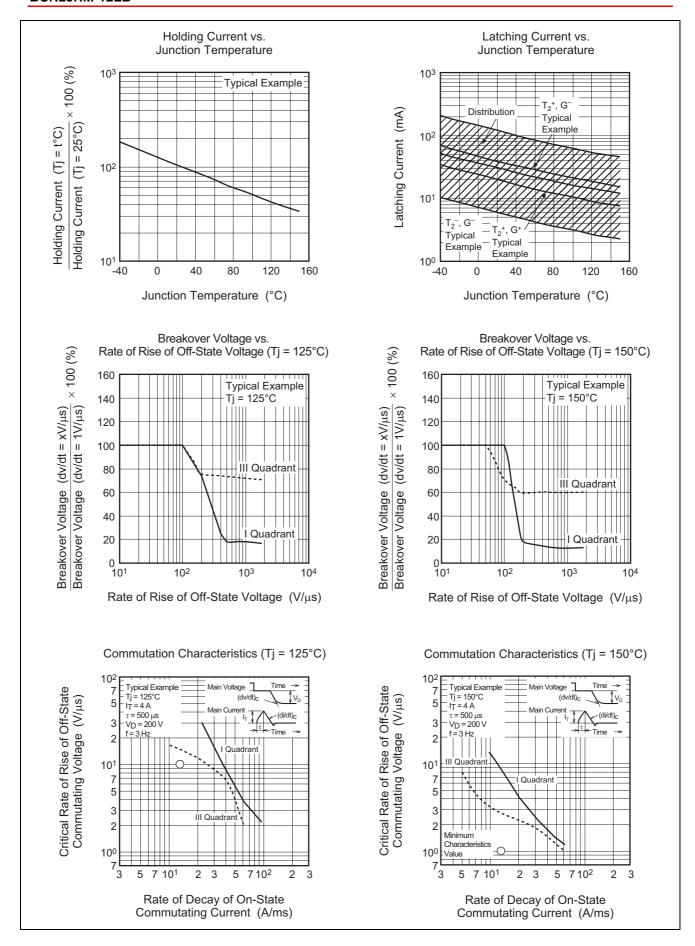
- 3. The contact thermal resistance $R_{th\;(c\text{-}f)}$ in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

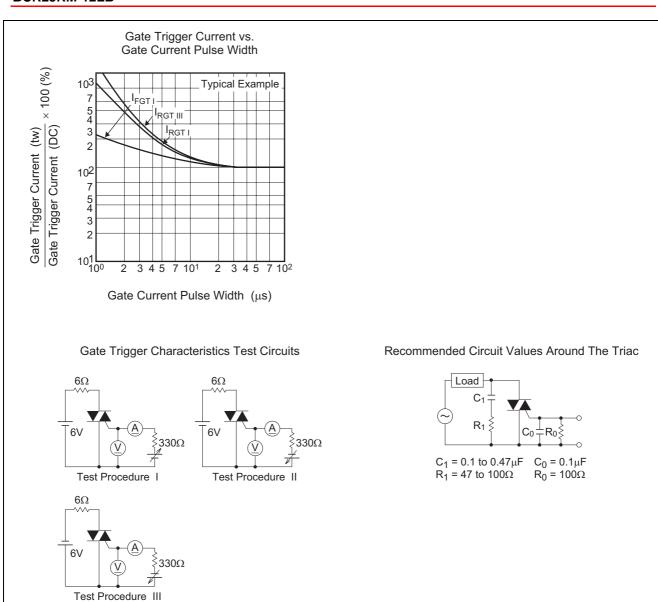
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125/150°C	Supply Voltage → Time
2. Rate of decay of on-state commutating current (di/dt)c = −13 A/ms	Main Current → (di/dt)c → Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time (dv/dt)c

Performance Curves

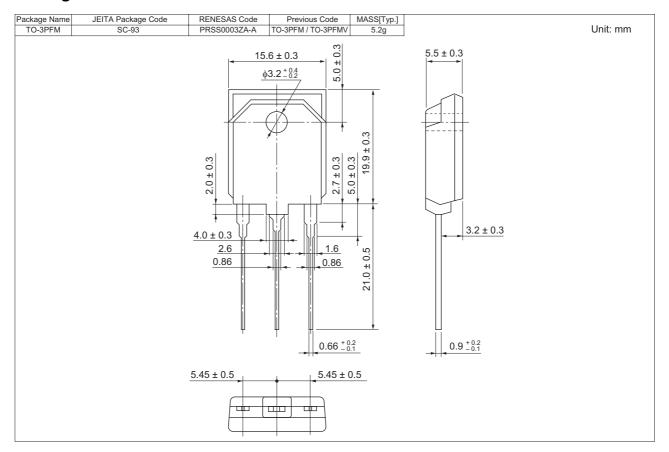








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Magazine (Tube)	30	Type name	BCR25RM-12LB

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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